

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".cls	US-PGPUB; USPAT	OR	ON	2005/11/25 17:36
L1	172341	substrate and gate	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/18 14:03
L2	281549	substrate and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:04
L3	57638	interlayer\$2 near (dielectric or insulat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:04
L4	8404268	vias or (via near hole\$1) or (contact hole\$1) or (contact near plug\$1) or (conductive near plug\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:05
L5	447621	I4 same (taper\$3 or slop\$3 or slant\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:05
L6	122028	(arc or antireflect\$) and (silicon or si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:06
L7	133	I2 and I3 and I5 and I6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:06

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L8	0	(trench or groove) with (tapered tapering taper) with conformal with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:07
L9	52	(trench or groove) with (tapered tapering taper) with polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:09
L10	43	(trench or groove) with (tapered tapering taper) with polysilicon	US-PGPUB; USPAT	OR	ON	2006/05/18 15:14
L11	30	I10 not dram	US-PGPUB; USPAT	OR	ON	2006/05/18 15:14
L12	4	(trench or groove) with (tapered tapering taper) with polysilicon with void	US-PGPUB; USPAT	OR	ON	2006/05/18 15:16
L13	0	(contact or hole) with (tapered tapering taper) with polysilicon with void	US-PGPUB; USPAT	OR	ON	2006/05/18 15:16
L14	3	(sidewall) with (tapered tapering taper) with polysilicon with void	US-PGPUB; USPAT	OR	ON	2006/05/18 15:20
L15	38	(contact) with (tapered tapering taper) with polysilicon	US-PGPUB; USPAT	OR	ON	2006/05/18 15:20
S1	2	("20050085086").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/17 12:51
S2	1052	257/734.ccls.	US-PGPUB; USPAT	OR	ON	2005/11/25 15:57
S3	811	S2 and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 16:59
S4	453	S3 and via	US-PGPUB; USPAT	OR	ON	2005/11/25 17:26
S5	100	S3 and via and gate	US-PGPUB; USPAT	OR	ON	2005/11/25 17:28
S6	6682	via near hole and gate	US-PGPUB; USPAT	OR	ON	2005/11/25 17:29
S7	3528	via near hole and gate and semiconductor near device	US-PGPUB; USPAT	OR	ON	2005/11/25 17:30

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S8	0	via near hole and gate and semiconductor near device and silicon near laye and substrate and dielectric and metal	US-PGPUB; USPAT	OR	ON	2005/11/25 17:30
S9	20751	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal	US-PGPUB; USPAT	OR	ON	2005/11/25 17:36
S10	14801	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas.	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S11	13023	((via near hole) or via) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S12	1892	(via near hole) and gate and semiconductor and device and silicon and layer and substrate and dielectric and metal and "257".clas. and @ad<="20031021"	US-PGPUB; USPAT	OR	ON	2005/11/25 17:37
S13	1	("6791187").PN.	US-PGPUB; USPAT	OR	OFF	2005/11/28 13:19
S14	0	("1761481986").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2005/11/28 13:19
S15	2	("0176148").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20
S16	0	(176148/1986).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20
S17	0	("1761481986").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 13:20

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S18	0	"1761481986"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:21
S19	7	176148/1986	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:47
S20	100	tapered near via near hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 13:47
S21	62	tapered near via near hole	US-PGPUB; USPAT	OR	ON	2005/11/28 13:50
S22	7	tapered near via near hole and anisotropically	US-PGPUB; USPAT	OR	ON	2005/11/28 16:20
S23	3742	257/774	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:21
S24	3108	257/773	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:21
S25	1948	257/734	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:22
S26	585	257/770	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24

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S27	1819	257/750	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
S28	5222	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
S29	1363	257/763	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
S30	2395	438/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 16:24
S31	2	("6791187").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/17 12:51
S32	28	("4840923" "4974040" "5036370" "5061985" "5150276" "5150278" "5196910" "5204286" "5281549" "5292677" "5302551" "5324681" "5346844" "5389568" "5414655" "5479054" "5561311" "5573965" "5605857" "5612254" "5623164" "5661344" "5689126" "5732009" "5760429" "5793076" "5874756" "6150689").PN. OR ("6791187"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 14:11
S33	39	("4649406" "4700457" "4742018").PN. OR ("4974040"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:10
S34	0	S32 and S33 and (taper tapered) and gate and silicon and etch	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:11

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S35	0	S32 and S33 and (taper tapered) and gate and silicon and (etch etching)	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:11
S36	0	S32 and S33 and (taper tapered)	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:11
S37	2008	(taper tapered) and gate and (etch and etching) and hole and via	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:11
S38	1911	(taper tapered) and gate and (etch and etching) and hole and via and silicon	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/17 15:12
S39	1911	(taper tapered) and gate and (etch and etching) and hole and via and silicon and (antireflective silicon dioxide oxide)	US-PGPUB; USPAT; USOCR	OR	ON	2006/05/18 14:03